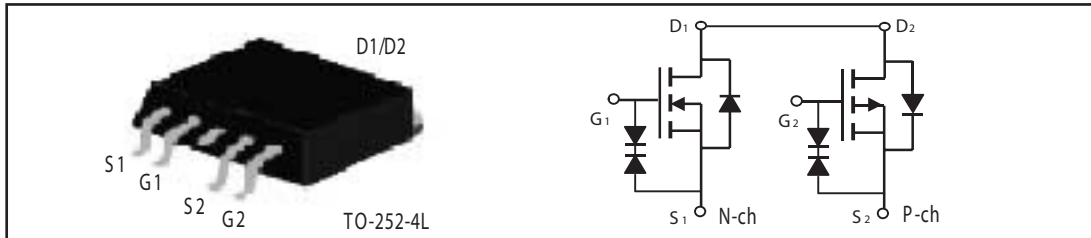




## Dual Enhancement Mode Field Effect Transistor ( N and P Channel)

PRODUCT SUMMARY (N-Channel)		
V <sub>DSS</sub>	I <sub>D</sub>	R <sub>DS(ON)</sub> ( mΩ ) Max
40V	16A	29 @ V <sub>GS</sub> = 10V
		39 @ V <sub>GS</sub> = 4.5V

PRODUCT SUMMARY (P-Channel)		
V <sub>DSS</sub>	I <sub>D</sub>	R <sub>DS(ON)</sub> ( mΩ ) Max
-40V	-12A	47 @ V <sub>GS</sub> = -10V
		64 @ V <sub>GS</sub> = -4.5V



### ABSOLUTE MAXIMUM RATINGS (T<sub>A</sub>=25°C unless otherwise noted)

Parameter	Symbol	N-Channel	P-Channel	Unit
Drain-Source Voltage	V <sub>DS</sub>	40	-40	V
Gate-Source Voltage	V <sub>GS</sub>	±20	±20	V
Drain Current-Continuous @ T <sub>c</sub>	I <sub>D</sub>	16	-12	A
		13.8	-10	A
-Pulsed <sup>a</sup>	I <sub>DM</sub>	50	-50	A
Drain-Source Diode Forward Current	I <sub>S</sub>	8	-6	A
Maximum Power Dissipation	P <sub>D</sub>	11		W
		7.7		
Operating Junction and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55 to 175		°C

### THERMAL CHARACTERISTICS

Thermal Resistance, Junction-to-Case	R <sub>θJC</sub>	13.6	°C/W
Thermal Resistance, Junction-to-Ambient	R <sub>θJA</sub>	120	°C/W

# STU407DH

N-Channel ELECTRICAL CHARACTERISTICS ( $T_A = 25\text{ }^{\circ}\text{C}$  unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ <sup>c</sup>	Max	Unit
OFF CHARACTERISTICS						
Drain-Source Breakdown Voltage	$BV_{DSS}$	$V_{GS}=0V, I_D=250\mu A$	40			V
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS}=32V, V_{GS}=0V$			1	$\mu A$
Gate-Body Leakage	$I_{GSS}$	$V_{GS}=\pm 20V, V_{DS}=0V$			$\pm 10$	$\mu A$
ON CHARACTERISTICS <sup>a</sup>						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=250\mu A$	1	1.8	3	V
Drain-Source On-State Resistance	$R_{DS(ON)}$	$V_{GS}=10V, I_D=8A$		21	29	m ohm
		$V_{GS}=4.5V, I_D=6A$		29	39	m ohm
On-State Drain Current	$I_{D(ON)}$	$V_{DS}=5V, V_{GS}=4.5V$	20			A
Forward Transconductance	$g_{FS}$	$V_{DS}=10V, I_D=8A$		15		S
DYNAMIC CHARACTERISTICS <sup>b</sup>						
Input Capacitance	$C_{ISS}$	$V_{DS}=20V, V_{GS}=0V$ $f=1.0MHz$		735		pF
Output Capacitance	$C_{OSS}$			120		pF
Reverse Transfer Capacitance	$C_{RSS}$			70		pF
Gate resistance	$R_g$	$V_{GS}=0V, V_{DS}=0V, f=1.0MHz$		0.36		ohm
SWITCHING CHARACTERISTICS <sup>b</sup>						
Turn-On Delay Time	$t_{D(ON)}$	$V_{DD}=20V$ $I_D=3A$ $V_{GS}=10V$ $R_{GEN}=3\text{ ohm}$		13		ns
Rise Time	$t_r$			15		ns
Turn-Off Delay Time	$t_{D(OFF)}$			26		ns
Fall Time	$t_f$			10		ns
Total Gate Charge	$Q_g$	$V_{DS}=20V, I_D=8A, V_{GS}=10V$		15		nC
		$V_{DS}=20V, I_D=8A, V_{GS}=4.5V$		7.2		nC
Gate-Source Charge	$Q_{gs}$	$V_{DS}=20V, I_D=8A$		2.0		nC
Gate-Drain Charge	$Q_{gd}$	$V_{GS}=10V$		3.8		nC

# STU407DH

P-Channel ELECTRICAL CHARACTERISTICS (TA = 25 °C unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ <sup>c</sup>	Max	Unit	
<b>OFF CHARACTERISTICS</b>							
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	V <sub>GS</sub> = 0V, I <sub>D</sub> = -250uA	-40			V	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> = -32V, V <sub>GS</sub> = 0V			-1	uA	
Gate-Body Leakage	I <sub>GSS</sub>	V <sub>GS</sub> = ±20V, V <sub>DS</sub> = 0V			±10	uA	
<b>ON CHARACTERISTICS<sup>a</sup></b>							
Gate Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = -250uA	-1	-1.6	-3	V	
Drain-Source On-State Resistance	R <sub>DS(ON)</sub>	V <sub>GS</sub> = -10V, I <sub>D</sub> = -6A		39	47	m ohm	
		V <sub>GS</sub> = -4.5V, I <sub>D</sub> = -4A		49	64	m ohm	
On-State Drain Current	I <sub>D(ON)</sub>	V <sub>DS</sub> = -5V, V <sub>GS</sub> = -10V	-20			A	
Forward Transconductance	g <sub>FS</sub>	V <sub>DS</sub> = -10V, I <sub>D</sub> = -6A		9		S	
<b>DYNAMIC CHARACTERISTICS<sup>b</sup></b>							
Input Capacitance	C <sub>ISS</sub>	V <sub>DS</sub> = -20V, V <sub>GS</sub> = 0V f = 1.0MHz		920		pF	
Output Capacitance	C <sub>OSS</sub>			135		pF	
Reverse Transfer Capacitance	C <sub>RSS</sub>			75		pF	
Gate resistance	R <sub>g</sub>	V <sub>GS</sub> = 0V, V <sub>DS</sub> = 0V, f = 1.0MHz		3.5		ohm	
<b>SWITCHING CHARACTERISTICS<sup>b</sup></b>							
Turn-On Delay Time	t <sub>D(ON)</sub>	V <sub>DD</sub> = -20V I <sub>D</sub> = -3A V <sub>GS</sub> = -10V R <sub>GEN</sub> = 3 ohm		12		ns	
Rise Time	t <sub>r</sub>			13		ns	
Turn-Off Delay Time	t <sub>D(OFF)</sub>				60		ns
Fall Time	t <sub>f</sub>				25		ns
Total Gate Charge	Q <sub>g</sub>	V <sub>DS</sub> = -20V, I <sub>D</sub> = -6A, V <sub>GS</sub> = -10V		15		nC	
		V <sub>DS</sub> = -20V, I <sub>D</sub> = -6A, V <sub>GS</sub> = -4.5V		7.2		nC	
Gate-Source Charge	Q <sub>gs</sub>	V <sub>DS</sub> = -20V, I <sub>D</sub> = -6 A		2		nC	
Gate-Drain Charge	Q <sub>gd</sub>	V <sub>GS</sub> = -10V		4.0		nC	

# STU407DH

ELECTRICAL CHARACTERISTICS ( $T_A=25^\circ\text{C}$  unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ <sup>c</sup>	Max	Unit
<b>DRAIN-SOURCE DIODE CHARACTERISTICS<sup>b</sup></b>						
Diode Forward Voltage	$V_{SD}$	$V_{GS} = 0V, I_S = 8A$ $V_{GS} = 0V, I_S = -6A$	N-Ch P-Ch	0.94 -0.87	1.2 -1.2	V

Notes

a. Pulse Test: Pulse Width  $\leq 300 \mu s$ , Duty Cycle  $\leq 2\%$ .

b. Guaranteed by design, not subject to production testing.

N-Channel

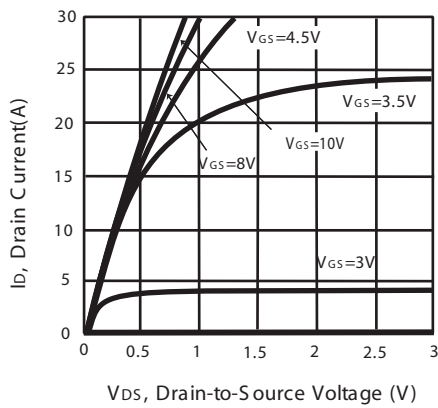


Figure 1. Output Characteristics

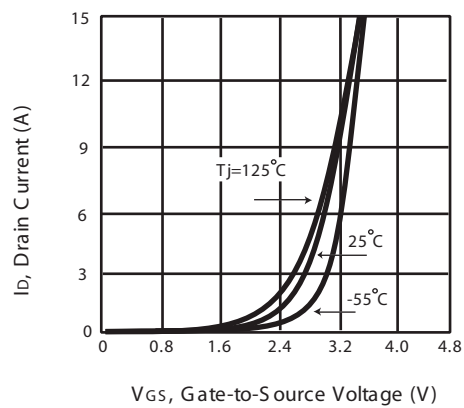


Figure 2. Transfer Characteristics

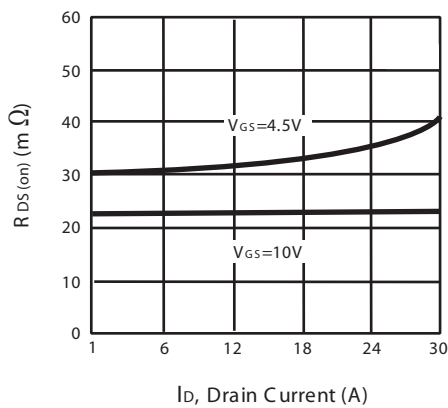


Figure 3. On-Resistance vs. Drain Current and Gate Voltage

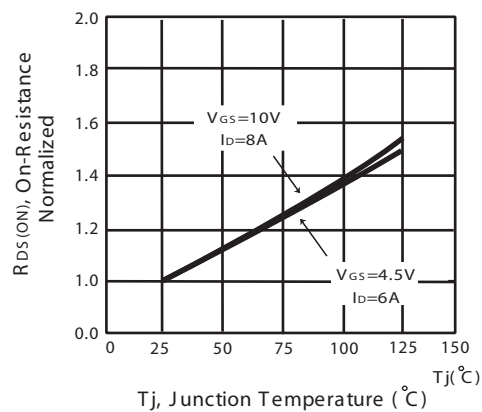


Figure 4. On-Resistance Variation with Drain Current and Temperature

# STU407DH

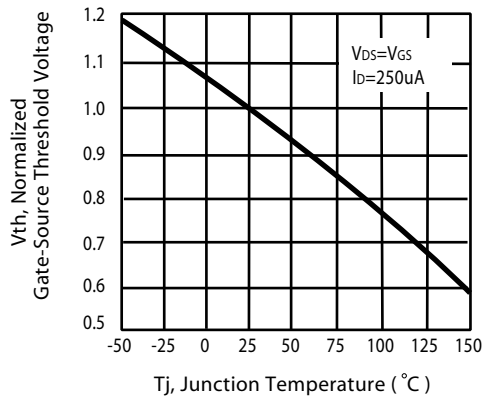


Figure 5. Gate Threshold Variation with Temperature

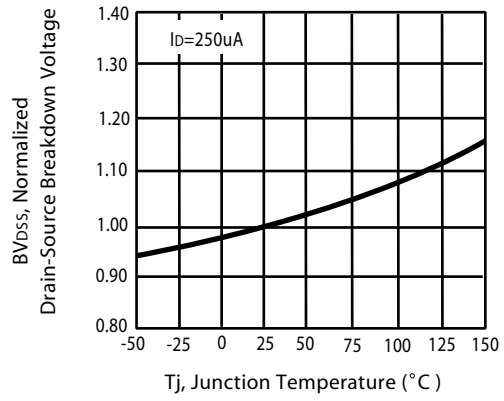


Figure 6. Breakdown Voltage Variation with Temperature

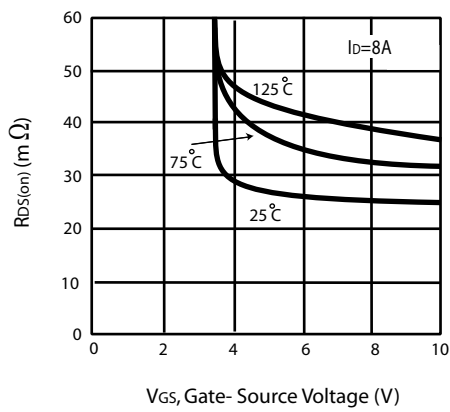


Figure 7. On-Resistance vs. Gate-Source Voltage

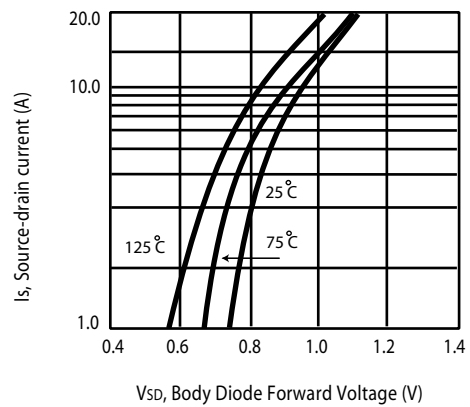


Figure 8. Body Diode Forward Voltage Variation with Source Current

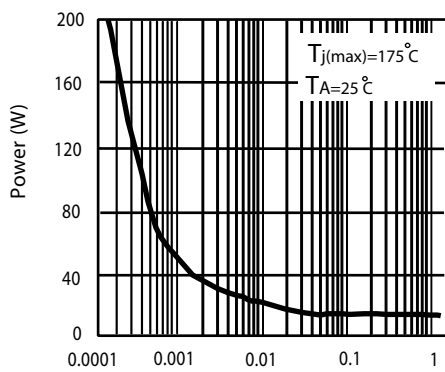


Figure 9. Single Pulse Power Rating Junction-to-Case

# STU407DH

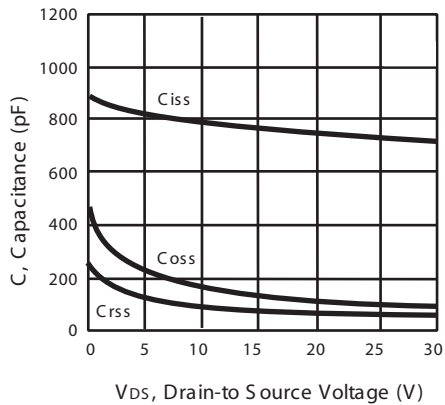


Figure 10. Capacitance

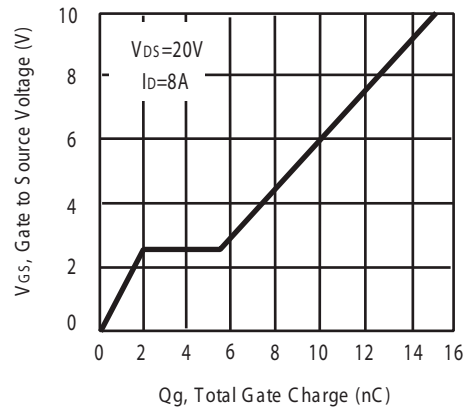


Figure 11. Gate Charge

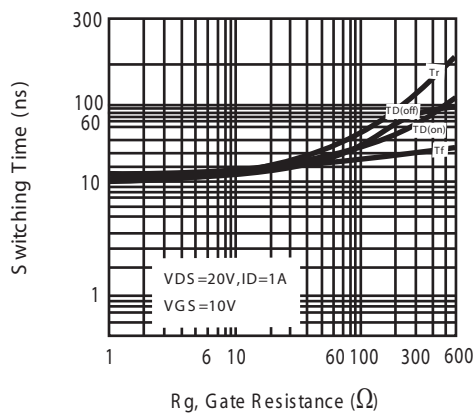


Figure 12. switching characteristics

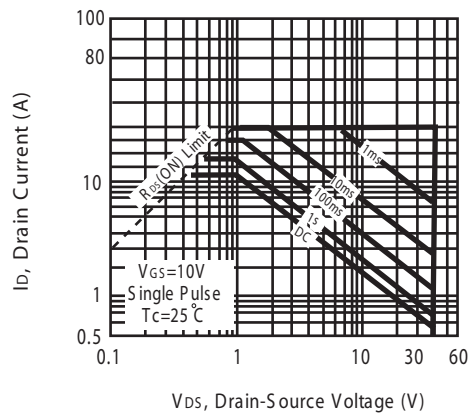


Figure 13. Maximum Safe Operating Area

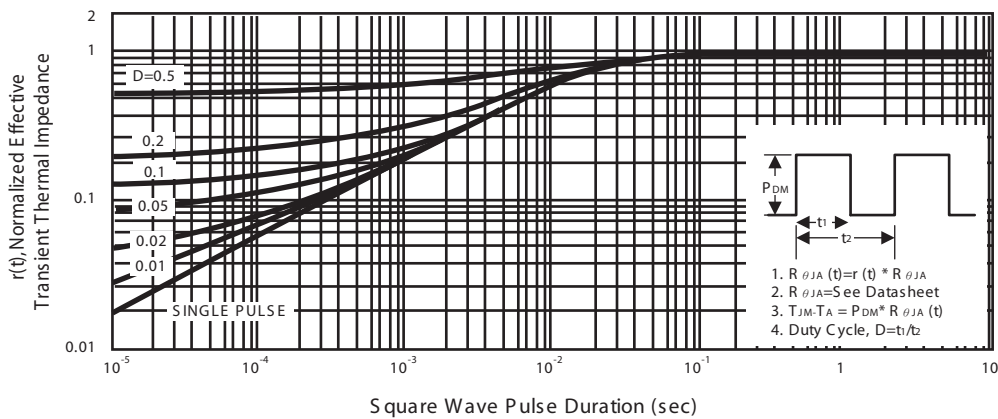


Figure 14. Normalized Thermal Transient Impedance Curve

# STU407DH

## P-Channel

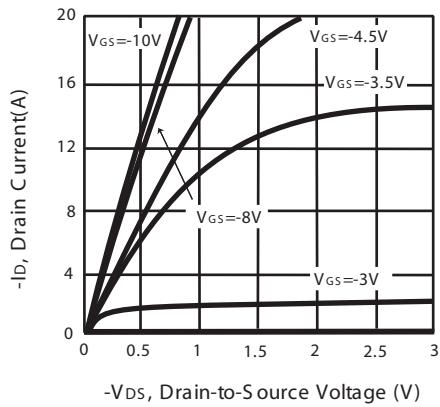


Figure 1. Output Characteristics

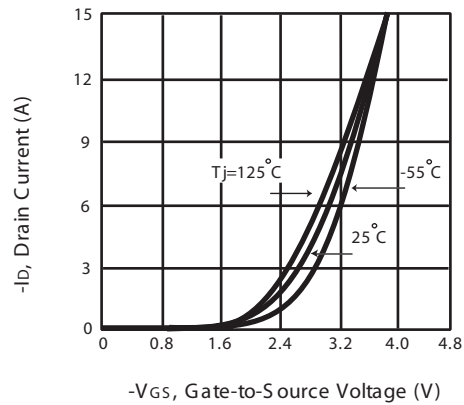


Figure 2. Transfer Characteristics

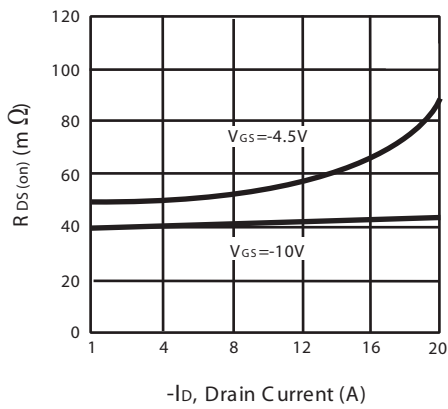


Figure 3. On-Resistance vs. Drain Current and Gate Voltage

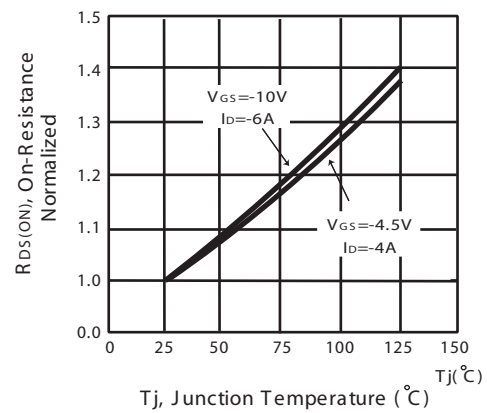


Figure 4. On-Resistance Variation with Drain Current and Temperature

# STU407DH

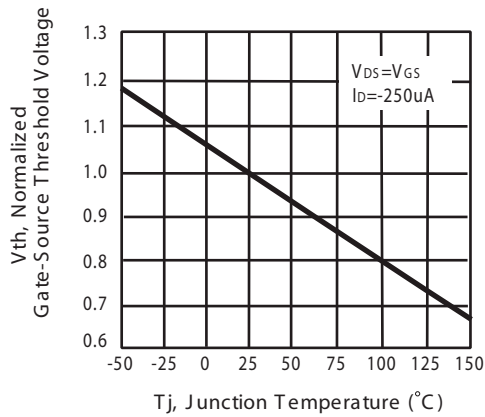


Figure 5. Gate Threshold Variation with Temperature

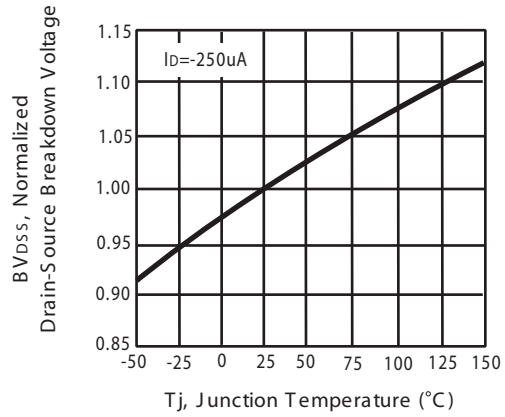


Figure 6. Breakdown Voltage Variation with Temperature

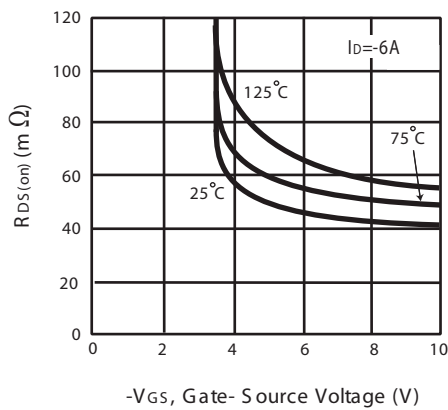


Figure 7. On-Resistance vs. Gate-Source Voltage

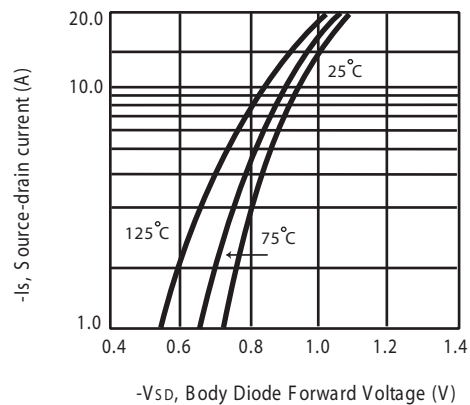


Figure 8. Body Diode Forward Voltage Variation with Source Current

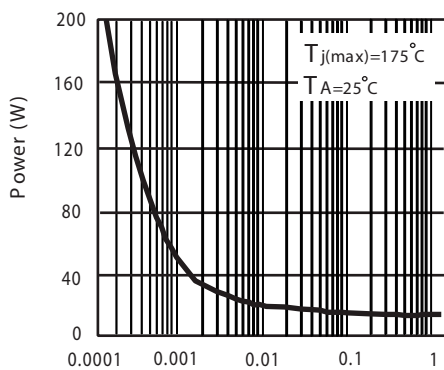


Figure 9. Single Pulse Power Rating Junction-to-Case



# STU407DH

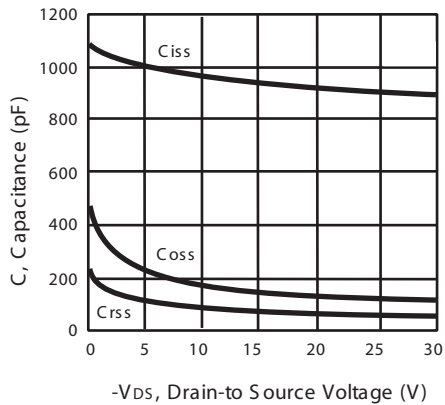


Figure 10. Capacitance

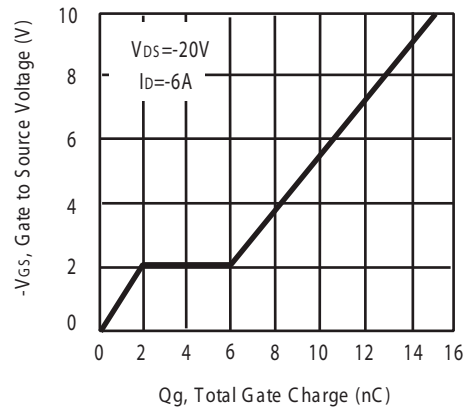


Figure 11. Gate Charge

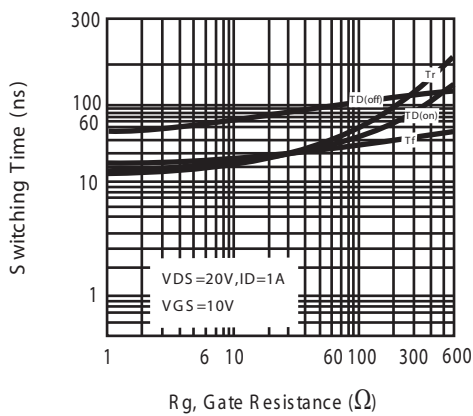


Figure 12. switching characteristics

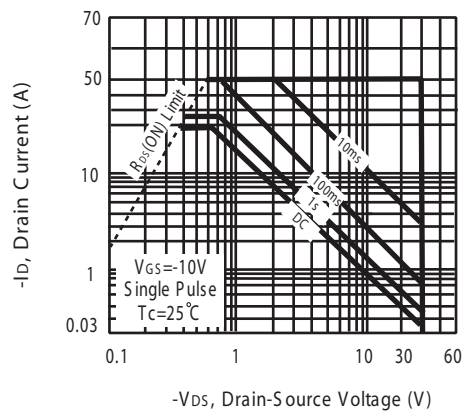


Figure 13. Maximum Safe Operating Area

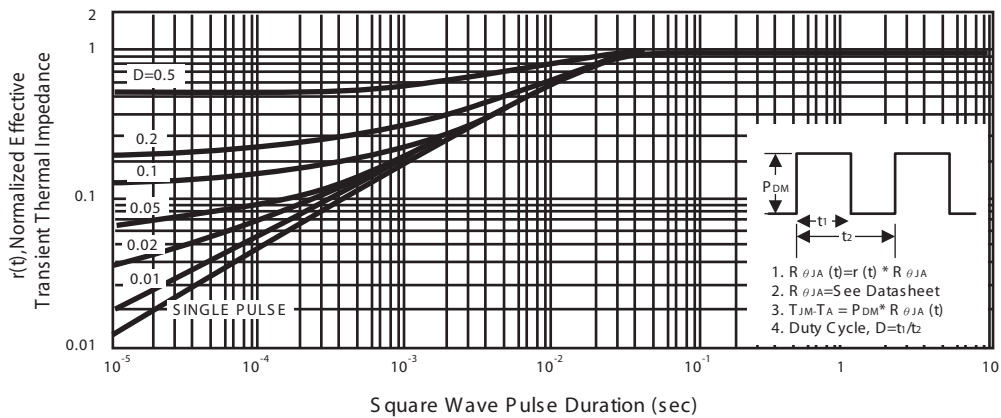
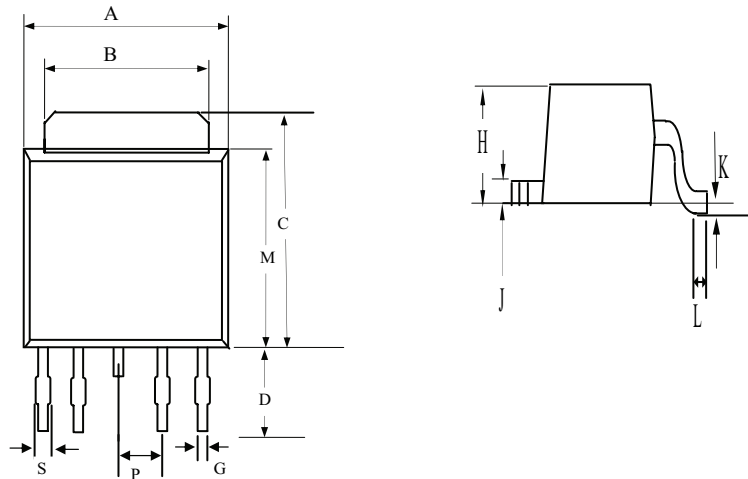


Figure 14. Normalized Thermal Transient Impedance Curve

# STU407DH

## PACKAGE OUTLINE DIMENSIONS

TO-252-4L

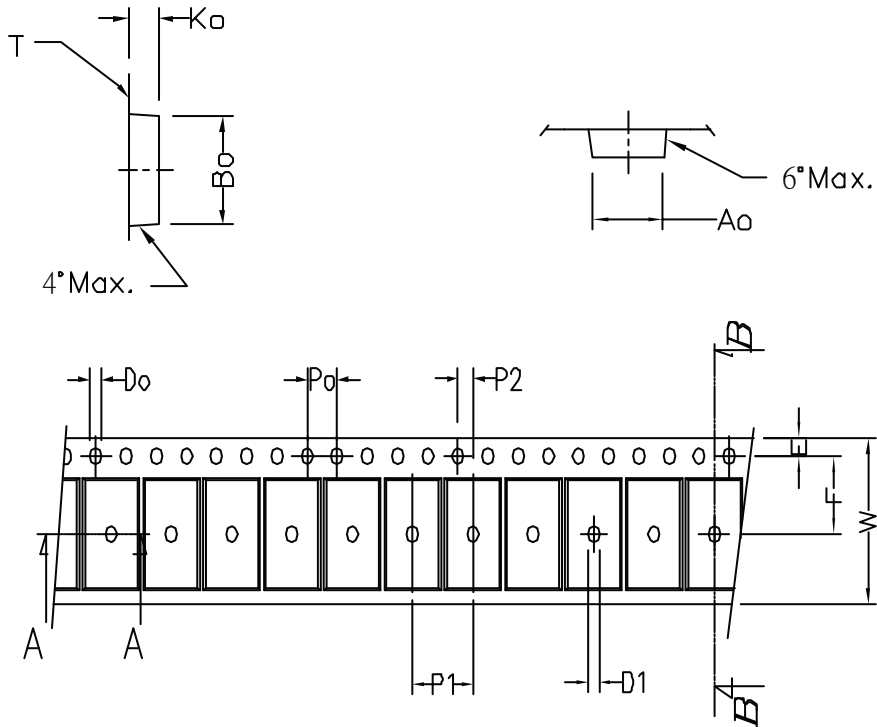


REF .	Millimeters	
	MIN	MAX
A	6.40	6.80
B	5.2	5.50
C	6.80	10.20
D	2.20	3.00
P	1.27 REF.	
S	0.50	0.80
G	0.40	0.60
H	2.20	2.40
J	0.45	0.60
K	0	0.15
L	0.90	1.50
M	5.40	5.80

# STU407DH

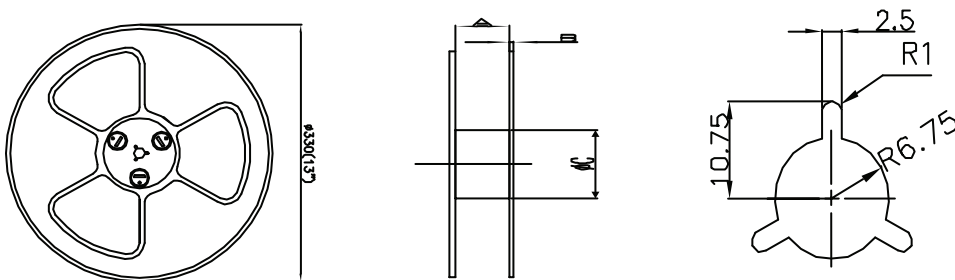
## TO-252-4L Tape and Reel Data

### TO-252-4L Carrier Tape



symbol	$A_0$	$B_0$	$K_0$	$P_0$	$P_1$	$P_2$	$T$
Spec	$6.96 \pm 0.1$	$10.49 \pm 0.1$	$2.79 \pm 0.1$	$4.0 \pm 0.1$	$8.0 \pm 0.10$	$2.0 \pm 0.05$	$0.33 \pm 0.013$
symbol	$E$	$F$	$D_0$	$D_1$	$W$	$10P_0$	
Spec	$1.75 \pm 0.1$	$7.5 \pm 0.05$	$1.55 \pm 0.05$	$1.5 \pm 0.25$	$16.0 \pm 0.3$ $16.0 \pm 0.1$	$40.0 \pm 0.2$	

### TO-252-4L Reel



UNIT:mm

Width of carrier tape	8	12	16	24	32	44	56
$A \pm 0.1$	9.4	13.4	17.4	25.4	33.4	45.4	57.4
$B$	2.3	2.3	2.3	2.3	2.3	2.3	2.3
$\phi C$	100	100	100	100	100	100	100